

PATENT

Atty. Dkt. No. APPM007034.P1/DSM/LOW K/JW

IN THE CLAIMS:

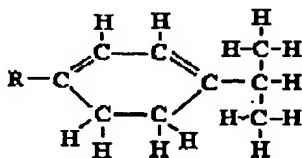
Please cancel claims 1-8 and 17-18 without prejudice and amend the claims as follows:

1-8. (Canceled)

9. (Currently Amended) The A method of claim 1 for depositing a dielectric film, comprising delivering a gas mixture comprising one or more linear, oxygen-free organosilicon compounds, one or more oxygen-free hydrocarbon compounds comprising one ring and one or two carbon-carbon double bonds in the ring, and one or more oxidizing gases comprising oxygen (O₂) to a substrate surface at deposition conditions sufficient to deposit a dielectric film comprising Si, O, and C on the substrate surface, wherein the one or more linear, oxygen-free organosilicon compounds comprises trimethylsilane and the one or more oxygen-free hydrocarbon compounds comprises alpha-terpinene.

10. (Previously Presented) The method of claim 9, wherein the one or more oxidizing gases consists of carbon dioxide and oxygen (O₂).

11. (Previously Presented) A method for depositing a dielectric film, comprising delivering a gas mixture comprising one or more linear, oxygen-free organosilicon compounds, one or more oxygen-free hydrocarbon compounds including the structure:



wherein R is selected from the group consisting of linear alkane groups having one to five carbons, and one or more oxidizing gases comprising oxygen (O₂) to a substrate

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surface at deposition conditions sufficient to deposit a dielectric film comprising Si, O, and C on the substrate surface.

12. (Original) The method of claim 11, wherein the one or more oxygen-free hydrocarbon compounds comprises alpha-terpinene.

13. (Currently Amended) The method of claim 11, wherein the one or more linear, oxygen-free organosilicon compounds comprises a member selected from the group consisting of methylsilane, dimethylsilane, trimethylsilane, tetramethylsilane, ethylsilane, disilanomethane, bis(methylsilano)methane, 1,2-disilanoethane, 1,2-bis(methylsilano)ethane, 2,2-disilanopropane, diethylsilane, propylsilane, vinylmethylsilane, 1,1,2,2-tetramethyldisilane, hexamethyldisilane, 1,1,2,3,3-pentamethyltrisilane, 1,3-bis(methylsilano)propane, 1,2-bis(dimethylsilano)ethane, 1,3-bis(dimethylsilano)propane, and combinations thereof.

14. (Original) The method of claim 11, wherein the linear alkane groups having one to five carbons are selected from the group consisting of methyl, ethyl, propyl, and isopropyl groups.

15. (Previously Presented) The method of claim 11, wherein the one or more oxidizing gases further comprises a member selected from the group consisting of ozone, carbon dioxide, carbon monoxide, water, nitrous oxide, 2,3-butanedione, and combinations thereof.

16. (Previously Presented) The method of claim 11, further comprising treating the dielectric film with an electron beam.

17-18. (Canceled)

19. (Currently Amended) ~~The A method of claim 17~~ for depositing a dielectric film, comprising:

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delivering a gas mixture comprising:

one or more linear, oxygen-free organosilicon compounds;

one or more oxygen-free hydrocarbon compounds comprising one ring and one or two carbon-carbon double bonds in the ring, wherein the one or more oxygen-free hydrocarbon compounds comprises alpha-terpinene;

and one or more oxidizing gases comprising oxygen (O₂) to a substrate surface at deposition conditions sufficient to deposit a dielectric film comprising Si, O, and C on the substrate surface; and

treating the dielectric film with an electron beam.

20. (Previously Presented) The method of claim 19, wherein the one or more linear, oxygen-free organosilicon compounds comprises trimethylsilane and the one or more oxidizing gases comprises carbon dioxide and oxygen (O₂).